

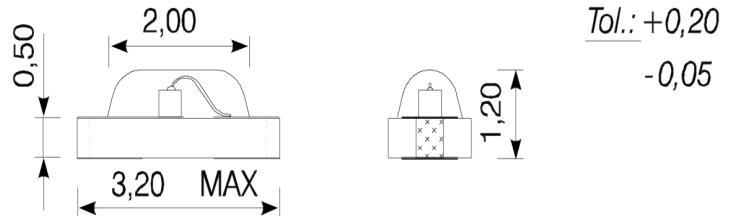
CR 50 UDB

Features

Solid State Ceramic Chip
 High Power Thermal Absorption
 Superior Light Uniformity Over 180°
 End-to-End and Side-to-Side Stackable to a pitch of 1.3mm
 Solderpads conform to Mil-Std 883B
 Caution: Static electricity and surge damages blue LED chip
 InGaN/SiC Material
 Water Clear Lens

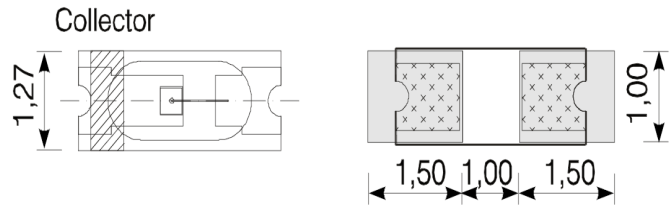
Applications

Ideal For Back-Light Applications
 Custom Configurations



Maximum Ratings (Ta=25°C)

Characteristic	Symbol	Max.	Unit
Forward Current	I _F	30	mA
Reverse Voltage	V _R	-	V
Power Dissipation	P _D	130.00	mW
Operating Temperature	T _{opr}	-25 ~ +80	°C
Storage Temperature	T _{stg}	-25 ~ +120	°C
Soldering Temperature	T _{sol}	250	°C
Soldering Time	-	for 10 sec. max	-

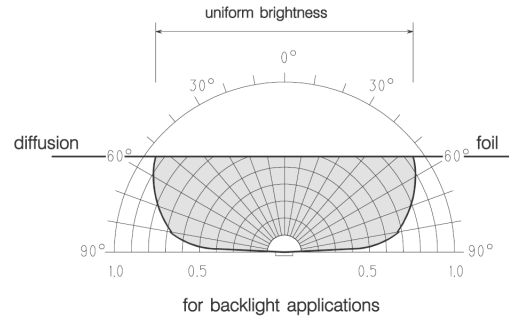
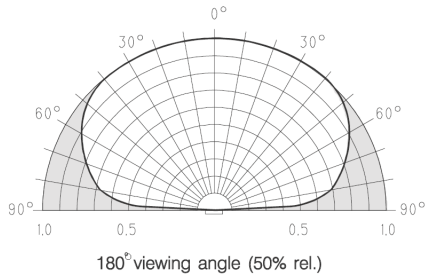


Opto-Electrical Characteristics (Ta=25°C)

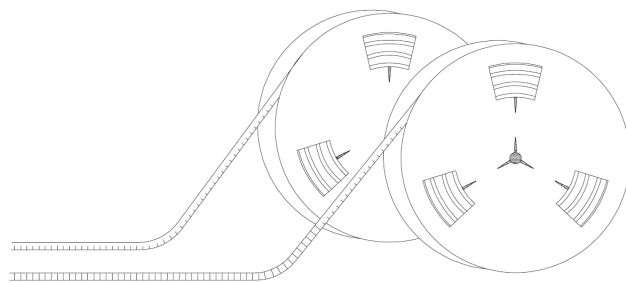
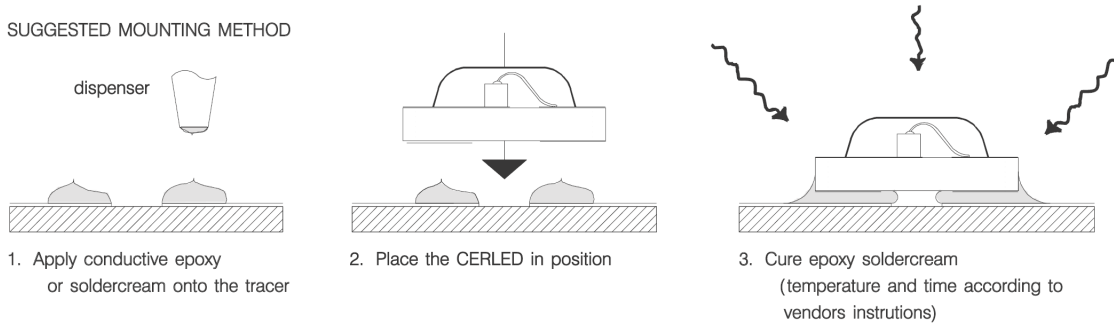
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F =20mA	-	3.70	4.50	V
Reverse Current	I _R	V _R =5V	-	-	10	μA
Luminous Intensity	I _v	I _F =20mA	5.00	30.00	-	mcd
Viewing Angle	2θ ^{1/2}	-	-	180°	-	deg.
Peak Wavelength	λ _p	I _F =20mA	-	465	-	nm
Dominant Wavelength	λ _d	I _F =20mA	-	470	-	nm
Spectral Line Half Width	Δλ	I _F =20mA	-	28	-	nm

Specifications are Subject to Change Without Notice

CR 50 UDB Graphs

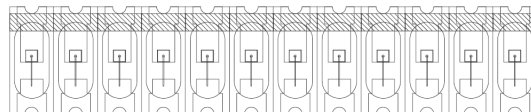


SUGGESTED MOUNTING METHOD



Special Packing:
standard 8mm blister tape

ARRAYS



code to order strips:
CR50 XX - 10
No of LEDs

Available in strips up to 12 CERLEDs with a max. pitch tolerance in spacing and linearity of $\pm 0,01$ mm between chip centers.